



August 1990

F100329

Low Power Octal ECL/TTL Bidirectional Translator with Register

General Description

The F100329 is an octal registered bidirectional translator designed to convert TTL logic levels to 100K ECL logic levels and vice versa. The direction of the translation is determined by the DIR input. A LOW on the output enable input (OE) holds the ECL outputs in a cut-off state and the TTL outputs at a high impedance level. The outputs change synchronously with the rising edge of the clock input (CP) even though only one output is enabled at the time.

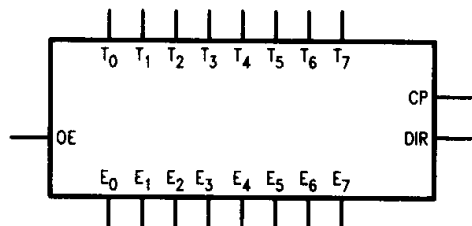
The cut-off state is designed to be more negative than a normal ECL LOW level. This allows the output emitter-followers to turn off when the termination supply is $-2.0V$, presenting a high impedance to the data bus. This high impedance reduces the termination power and prevents loss of low state noise margin when several loads share the bus.

The F100329 is designed with FAST® TTL output buffers, featuring optimal DC drive and capable of quickly charging and discharging highly capacitive loads. All inputs have $50\text{ k}\Omega$ pull-down resistors.

Features

- Bidirectional translation
- ECL high impedance outputs
- Registered outputs
- FAST TTL outputs
- TRI-STATE® outputs
- Voltage compensated operating range = $-4.2V$ to $-5.7V$

Logic Symbol

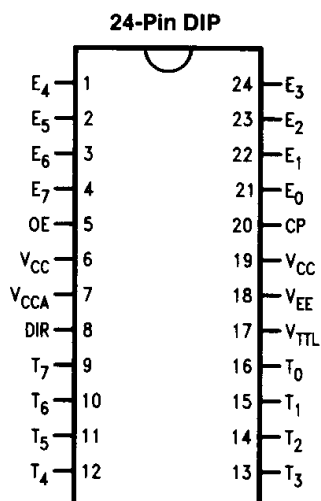


TL/F/10583-1

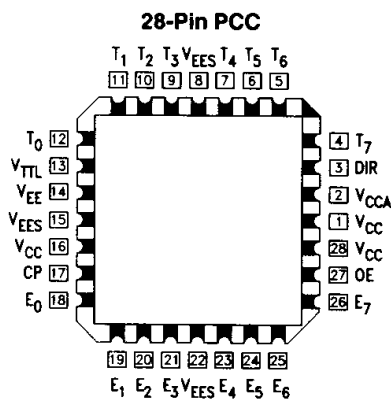
Pin Names	Description
E ₀ –E ₇	ECL Data I/O
T ₀ –T ₇	TTL Data I/O
OE	Output Enable Input
CP	Clock Pulse Input (Active Rising Edge)
DIR	Direction Control Input

All pins function at 100K ECL levels except for T₀–T₇.

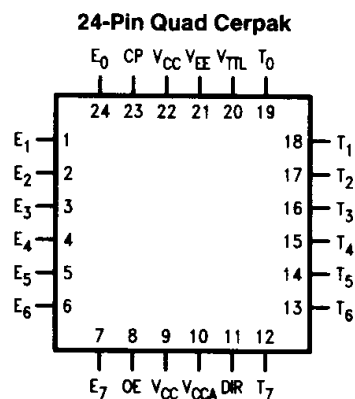
Connection Diagrams



TL/F/10583-2



TL/F/10583-3

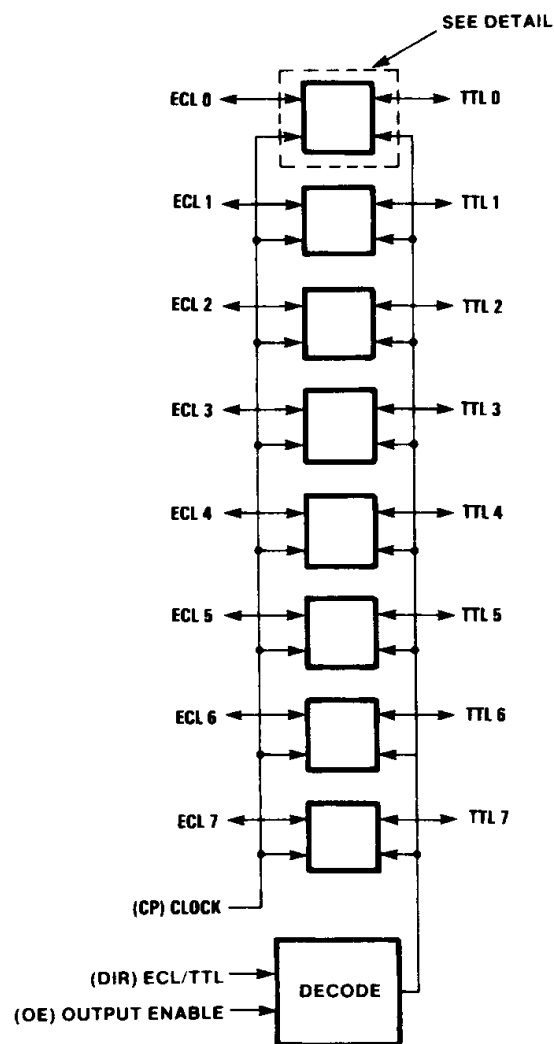


TL/F/10583-4

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F100329 Low Power Octal ECL/TTL Bidirectional Translator with Register

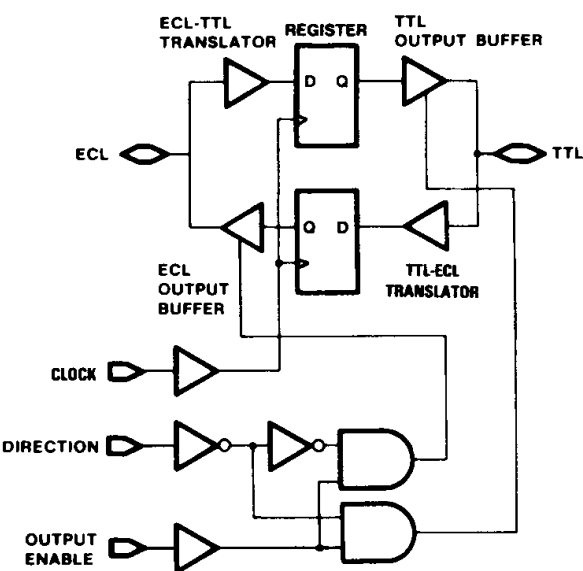
Functional Diagram



Note: DIR and OE use ECL logic levels

TL/F/10583-5

Detail



TL/F/10583-6

Truth Table

OE	DIR	CP	ECL Port	TTL Port	Notes
L	L	X	Input	Z	1, 3
L	H	X	LOW (Cut-Off)	Input	2, 3
H	L		L	L	1
H	L		H	H	1
H	L	L	X	NC	1, 3
H	H		L	L	2
H	H		H	H	2
H	H	L	NC	X	2, 3

H = HIGH Voltage Level
L = LOW Voltage Level
X = Don't Care
Z = High Impedance
 = LOW-to-HIGH Clock Transition
NC = No Change

Note 1: ECL input to TTL output mode.
Note 2: TTL input to ECL output mode.
Note 3: Retains data present before CP.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Storage Temperature (T_{STG})	–65°C to +150°C
Maximum Junction Temperature (T_J)	
Ceramic	+175°C
Plastic	+150°C
V_{EE} Pin Potential to Ground Pin	–7.0V to +0.5V
V_{TTL} Pin Potential to Ground Pin	+6.0V to –0.5V
ECL Input Voltage (DC)	V_{EE} to +0.5V
ECL Output Current (DC Output HIGH)	–50 mA
TTL Input Voltage (Note 4)	–0.5V to +7.0V
TTL Input Current (Note 4)	–30 mA to +5.0 mA

Voltage Applied to Output in HIGH State	
TRI-STATE Output	–0.5V to +5.5V
Current Applied to TTL Output in LOW State (Max)	Twice the Rated I_{OL} (mA)
ESD (Note 2)	≥2000V

Recommended Operating Conditions

Case Temperature (T_C)	
Commercial	0°C to +85°C
Military	–55°C to +125°C
ECL Supply Voltage (V_{EE})	
Commercial	–5.7V to –4.2V
Military	–5.7V to –4.2V
TTL Supply Voltage (V_{TTL})	
Commercial	+4.5V to +5.5V
Military	+4.5V to +5.5V

Commercial Version

TTL-to-ECL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{CC} = V_{CCA} = GND$, $T_C = 0^\circ C$ to $+85^\circ C$, $V_{TTL} = +4.5V$ to $+5.5V$ (Note 3)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{OH}	Output HIGH Voltage	–1025	–955	–870	mV	$V_{IN} = V_{IH}$ (Max) or V_{IL} (Min) Loading with 50Ω to –2V
V_{OL}	Output LOW Voltage	–1830	–1705	–1620	mV	
	Cutoff Voltage		–2000	–1950	mV	OE or DIR LOW, $V_{IN} = V_{IH}$ (Max) or V_{IL} (Min), Loading with 50Ω to –2V
V_{OHC}	Output HIGH Voltage Corner Point HIGH	–1035			mV	$V_{IN} = V_{IH}$ (Min) or V_{IL} (Max) Loading with 50Ω to –2V
V_{OLC}	Output LOW Voltage Corner Point LOW			–1610	mV	
V_{IH}	Input HIGH Voltage	2.0		5.0	V	Over V_{TTL} , V_{EE} , T_C Range
V_{IL}	Input LOW Voltage	0		0.8	V	Over V_{TTL} , V_{EE} , T_C Range
I_{IH}	Input HIGH Current			70	μA	$V_{IN} = +2.7V$
	Breakdown Test			1.0	mA	$V_{IN} = +5.5V$
I_{IL}	Input LOW Current	–700			μA	$V_{IN} = +0.5V$
V_{FCD}	Input Clamp Diode Voltage	–1.2			V	$I_{IN} = -18$ mA
I_{EE}	V_{EE} Supply Current					LE LOW, OE and DIR HIGH Inputs Open
		–189		–94	mA	$V_{EE} = -4.2V$ to $-4.8V$
		–199		–94		$V_{EE} = -4.2V$ to $-5.7V$

Note 1: Absolute maximum ratings are those values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: ESD testing conforms to MIL-STD-883, Method 3015.

Note 3: The specified limits represent the “worst case” value for the parameter. Since these values normally occur at the temperature extremes, additional noise immunity and guardbanding can be achieved by decreasing the allowable system operating ranges. Conditions for testing shown in the tables are chosen to guarantee operation under “worst case” conditions.

Note 4: Either voltage limit or current limit is sufficient to protect inputs.

Commercial Version (Continued)

ECL-to-TTL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{CC} = V_{CCA} = GND$, $T_C = 0^\circ C$ to $+85^\circ C$, $C_L = 50$ pF, $V_{TTL} = +4.5V$ to $+5.5V$ (Note 3)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
V_{OH}	Output High Voltage	2.7 2.4	3.1 2.9		V V	$I_{OH} = -3$ mA, $V_{TTL} = 4.75V$ $I_{OH} = -3$ mA, $V_{TTL} = 4.50V$
V_{OL}	Output Low Voltage		0.3	0.5	V	$I_{OL} = 24$ mA, $V_{TTL} = 4.50V$
V_{IH}	Input High Voltage	-1165		-870	mV	Guaranteed HIGH Signal for All Inputs
V_{IL}	Input Low Voltage	-1830		-1475	mV	Guaranteed LOW Signal for All Inputs
I_{IH}	Input High Current			350	μA	$V_{IN} = V_{IH}$ (Max)
I_{IL}	Input Low Current	0.50			μA	$V_{IN} = V_{IL}$ (Min)
I_{OZHT}	TRI-STATE Current Output High			70	μA	$V_{OUT} = +2.7V$
I_{OZLT}	TRI-STATE Current Output Low	-700			μA	$V_{OUT} = +0.5V$
I_{OS}	Output Short-Circuit Current	-150		-60	mA	$V_{OUT} = 0.0V$, $V_{TTL} = +5.5V$
I_{TTL}	V_{TTL} Supply Current			74 49 67	mA mA mA	TTL Outputs Low TTL Outputs High TTL Outputs in TRI-STATE

Ceramic Dual-In-Line Package TTL-to-ECL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $V_{CC} = V_{CCA} = GND$

Symbol	Parameter	$T_C = 0^\circ C$		$T_C = 25^\circ C$		$T_C = 85^\circ C$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
f_{max}	Max Toggle Frequency	350		350		350		MHz	
t_{PLH} t_{PHL}	CP to E_n	1.7	3.6	1.7	3.7	1.9	3.9	ns	Figures 1 & 2
t_{PZH}	OE to E_n (Cutoff to HIGH)	1.3	4.2	1.5	4.4	1.7	4.8	ns	Figures 1 & 2
t_{PHZ}	OE to E_n (HIGH to Cutoff)	1.5	4.5	1.6	4.5	1.6	4.6	ns	Figures 1 & 2
t_{PHZ}	DIR to E_n (HIGH to Cutoff)	1.6	4.3	1.6	4.3	1.7	4.5	ns	Figures 1 & 2
t_{set}	T_n to CP	1.1		1.1		1.1		ns	Figures 1 & 2
t_{hold}	T_n to CP	2.1		2.1		2.1		ns	Figures 1 & 2
$t_{pw(H)}$	Pulse Width CP	2.1		2.1		2.1		ns	Figures 1 & 2
t_{TLH} t_{THL}	Transition Time 20% to 80%, 80% to 20%	0.6	1.6	0.6	1.6	0.6	1.6	ns	Figures 1 & 2

Commercial Version (Continued)

Ceramic Dual-In-Line Package ECL-to-TTL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $V_{CC} = V_{CCA} = GND$, $C_L = 50$ pF

Symbol	Parameter	$T_C = 0^\circ C$		$T_C = 25^\circ C$		$T_C = 85^\circ C$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
f_{max}	Max Toggle Frequency	125		125		125		MHz	
t_{PLH} t_{PHL}	CP to T_n	3.1	7.2	3.1	7.2	3.3	7.7	ns	Figures 3 & 4
t_{PZH} t_{PZL}	OE to T_n (Enable Time)	3.4 3.8	8.45 9.2	3.7 4.0	8.95 9.2	4.0 4.3	9.7 9.95	ns	Figures 3 & 5
t_{PHZ} t_{PLZ}	OE to T_n (Disable Time)	3.2 3.0	8.95 7.7	3.3 3.4	8.95 8.7	3.5 4.1	9.2 9.95	ns	Figures 3 & 5
t_{PHZ} t_{PLZ}	DIR to T_n (Disable Time)	2.7 2.8	8.2 7.45	2.8 3.1	8.7 7.95	3.1 4.0	8.95 9.2	ns	Figures 3 & 6
t_{set}	E_n to CP	1.1		1.1		1.1		ns	Figures 3 & 4
t_{hold}	E_n to CP	2.1		2.1		2.6		ns	Figures 3 & 4
$t_{pw(H)}$	Pulse Width CP	4.1		4.1		4.1		ns	Figures 3 & 4

PCC and Cerpak TTL-to-ECL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	$T_C = 0^\circ C$		$T_C = 25^\circ C$		$T_C = 85^\circ C$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
f_{max}	Max Toggle Frequency	350		350		350		MHz	
t_{PLH} t_{PHL}	CP to E_n	1.7	3.4	1.7	3.5	1.9	3.7	ns	Figures 1 & 2
t_{PZH}	OE to E_n (Cutoff to HIGH)	1.3	4.0	1.5	4.2	1.7	4.6	ns	Figures 1 & 2
t_{PHZ}	OE to E_n (HIGH to Cutoff)	1.5	4.3	1.6	4.3	1.6	4.4	ns	Figures 1 & 2
t_{PHZ}	DIR to E_n (HIGH to Cutoff)	1.6	4.1	1.6	4.1	1.7	4.3	ns	Figures 1 & 2
t_{set}	T_n to CP	1.0		1.0		1.0		ns	Figures 1 & 2
t_{hold}	T_n to CP	2.0		2.0		2.0		ns	Figures 1 & 2
$t_{pw(H)}$	Pulse Width CP	2.0		2.0		2.0		ns	Figures 1 & 2
t_{TLH} t_{THL}	Transition Time 20% to 80%, 80% to 20%	0.6	1.6	0.6	1.6	0.6	1.6	ns	Figures 1 & 2

Commercial Version (Continued)

PCC and Cerpak ECL-to-TTL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $C_L = 50$ pF

Symbol	Parameter	$T_C = 0^\circ C$		$T_C = 25^\circ C$		$T_C = 85^\circ C$		Units	Conditions
		Min	Max	Min	Max	Min	Max		
f_{max}	Max Toggle Frequency	125		125		125		MHz	
t_{PLH} t_{PHL}	CP to T_n	3.1	7.0	3.1	7.0	3.3	7.5	ns	Figures 3 & 4
t_{pZH} t_{pZL}	OE to T_n (Enable Time)	3.4 3.8	8.25 9.0	3.7 4.0	8.75 9.0	4.0 4.3	9.5 9.75	ns	Figures 3 & 5
t_{PHZ} t_{PLZ}	OE to T_n (Disable Time)	3.2 3.0	8.75 7.5	3.3 3.4	8.75 8.5	3.5 4.1	9.0 9.75	ns	Figures 3 & 5
t_{PHZ} t_{PLZ}	DIR to T_n (Disable Time)	2.7 2.8	8.0 7.25	2.8 3.1	8.5 7.75	3.1 4.0	8.75 9.0	ns	Figures 3 & 6
t_{set}	E_n to CP	1.0		1.0		1.0		ns	Figures 3 & 4
t_{hold}	E_n to CP	2.0		2.0		2.5		ns	Figures 3 & 4
$t_{pw(H)}$	Pulse Width CP	4.0		4.0		4.0		ns	Figures 3 & 4

Military Version-Preliminary

TTL-to-ECL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{CC} = V_{CCA} = GND$, $T_C = -55^\circ C$ to $+125^\circ C$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	Min	Max	Units	T _C	Conditions		Notes
V _{OH}	Output HIGH Voltage	− 1025	− 870	mV	0°C to + 125°C	V _{IN} = V _{IH} (Max) or V _{IL} (Min)	Loading with 50Ω to − 2.0V	1, 2, 3
		− 1085	− 870	mV	− 55°C			
V _{OL}	Output LOW Voltage	− 1830	− 1620	mV	0°C to + 125°C	OE or DIR LOW		
		− 1830	− 1555	mV	− 55°C			
	Cutoff Voltage		− 1950	mV	0°C to + 125°C			
			− 1850	mV	− 55°C			
V _{OHC}	Output HIGH Voltage	− 1035		mV	0°C to + 125°C	V _{IN} = V _{IH} (Min) or V _{IL} (Max)	Loading with 50Ω to − 2.0V	1, 2, 3
		− 1085		mV	− 55°C			
V _{OLC}	Output LOW Voltage		− 1610	mV	0°C to + 125°C			
			− 1555	mV	− 55°C			
V _{IH}	Input HIGH Voltage	2.0		V	− 55°C to + 125°C	Over V _{TTL} , V _{EE} , T _C Range		1, 2, 3, 4
V _{IL}	Input LOW Voltage		0.8	V	− 55°C to + 125°C	Over V _{TTL} , V _{EE} , T _C Range		1, 2, 3, 4
I _{IH}	Input HIGH Current		70	μA	− 55°C to + 125°C	V _{IN} = + 2.7V		1, 2, 3
	Breakdown Test		1.0	mA	− 55°C to + 125°C	V _{IN} = + 5.5V		
I _{IL}	Input LOW Current	− 1.0		mA	− 55°C to + 125°C	V _{IN} = + 0.5V		1, 2, 3
V _{FCD}	Input Clamp Diode Voltage	− 1.2		V	− 55°C to + 125°C	I _{IN} = − 18 mA		1, 2, 3
I _{EE}	V _{EE} Supply Current	− 210 − 220	− 70 − 70	mA	− 55°C to + 125°C	LE LOW, OE and DIR HIGH Inputs Open V _{EE} = − 4.2V to − 4.8V V _{EE} = − 4.2V to − 5.7V		1, 2, 3

Military Version-Preliminary (Continued)

ECL-to-TTL DC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{CC} = V_{CCA} = GND$, $T_C = -55^{\circ}C$ to $+125^{\circ}C$, $C_L = 50$ pF, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	Min	Max	Units	T_C	Conditions	Notes
V_{OH}	Output HIGH Voltage	2.5 2.4		mV	$-55^{\circ}C$ to $+125^{\circ}C$	$I_{OH} = -1$ mA, $V_{TTL} = 4.50V$ $I_{OH} = -3$ mA, $V_{TTL} = 4.50V$	1, 2, 3
V_{OL}	Output LOW Voltage		0.5	mV	$-55^{\circ}C$ to $+125^{\circ}C$	$I_{OL} = 24$ mA, $V_{TTL} = 4.50V$	
V_{IH}	Input HIGH Voltage	-1165	-870	mV	$-55^{\circ}C$ to $+125^{\circ}C$	Guaranteed HIGH Signal for All Inputs	1, 2, 3, 4
V_{IL}	Input LOW Voltage	-1830	-1475	mV	$-55^{\circ}C$ to $+125^{\circ}C$	Guaranteed LOW Signal for All Inputs	1, 2, 3, 4
I_{IH}	Input HIGH Current		350	μA	$0^{\circ}C$ to $+125^{\circ}C$	$V_{EE} = -5.7V$ $V_{IN} = V_{IH} (Max)$	1, 2, 3
			500	μA	$-55^{\circ}C$		
I_{IL}	Input LOW Current	0.50		μA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{EE} = -4.2V$ $V_{IN} = V_{IL} (Min)$	1, 2, 3
I_{OZHT}	TRI-STATE Current Output High		70	μA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{OUT} = +2.7V$	1, 2, 3
I_{OZLT}	TRI-STATE Current Output Low		-1.0	mA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{OUT} = +0.5V$	1, 2, 3
I_{OS}	Output Short-Circuit Current	-150	-60	mA	$-55^{\circ}C$ to $+125^{\circ}C$	$V_{OUT} = 0.0V$, $V_{TTL} = +5.5V$	1, 2, 3
I_{TTL}	V_{TTL} Supply Current		75	mA	$-55^{\circ}C$ to $+125^{\circ}C$	TTL Outputs Low TTL Outputs High TTL Outputs in TRI-STATE	1, 2, 3
			50	mA			
			70	mA			

Note 1: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals $-55^{\circ}C$), then testing immediately without allowing for the junction temperature to stabilize due to heat dissipation after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

Note 2: Screen tested 100% on each device at $-55^{\circ}C$, $+25^{\circ}C$, and $+125^{\circ}C$, Subgroups 1, 2, 3, 7, and 8.

Note 3: Sample tested (Method 5005, Table I) on each manufactured lot at $-55^{\circ}C$, $+25^{\circ}C$, and $+125^{\circ}C$, Subgroups A1, 2, 3, 7, and 8.

Note 4: Guaranteed by applying specified input condition and testing V_{OH}/V_{OL} .

Military Version-Preliminary (Continued)

Ceramic Dual-In-Line Package TTL-to-ECL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $V_{CC} = V_{CCA} = GND$

Symbol	Parameter	$T_C = -55^{\circ}C$		$T_C = 25^{\circ}C$		$T_C = +125^{\circ}C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
f_{max}	Max Toggle Frequency	250		250		250		MHz		4
t_{PLH} t_{PHL}	CP to E_n	1.3	3.8	1.6	3.7	1.9	4.3	ns	Figures 1 & 2	1, 2, 3
t_{pZH}	OE to E_n (Cutoff to HIGH)	1.0	4.3	1.5	4.4	1.7	5.1	ns	Figures 1 & 2	
t_{pHZ}	OE to E_n (HIGH to Cutoff)	1.5	5.0	1.6	4.5	1.6	5.0	ns	Figures 1 & 2	
t_{pHZ}	DIR to E_n (HIGH to Cutoff)	1.6	4.7	1.6	4.3	1.7	4.7	ns	Figures 1 & 2	
t_{set}	T_n to CP	2.5		2.0		2.5		ns	Figures 1 & 2	4
t_{hold}	T_n to CP	2.5		2.0		2.5		ns	Figures 1 & 2	
$t_{pw(H)}$	Pulse Width CP	2.5		2.0		2.5		ns	Figures 1 & 2	
t_{TLH} t_{THL}	Transition Time 20% to 80%, 80% to 20%	0.4	2.3	0.5	2.1	0.4	2.4	ns	Figures 1 & 2	

Ceramic Dual-In-Line Package ECL-to-TTL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $V_{CC} = V_{CCA} = GND$, $C_L = 50$ pF

Symbol	Parameter	$T_C = -55^{\circ}C$		$T_C = 25^{\circ}C$		$T_C = +125^{\circ}C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
f_{max}	Max Toggle Frequency	200		200		100		MHz		4
t_{PLH} t_{PHL}	CP to T_n	3.1	8.0	3.1	7.3	3.3	8.0	ns	Figures 3 & 4	1, 2, 3
t_{pZH} t_{pZL}	OE to T_n (Enable Time)	3.4 3.7	9.1 9.5	3.7 4.0	9.0 9.3	4.0 4.3	10.1 10.4	ns	Figures 3 & 5	
t_{pHZ} t_{PLZ}	OE to T_n (Disable Time)	3.2 3.0	10.0 9.8	3.3 3.4	9.0 8.8	3.5 4.1	9.3 10.4	ns	Figures 3 & 5	
t_{pHZ} t_{PLZ}	DIR to T_n (Disable Time)	2.6 2.7	9.5 8.7	2.8 3.1	8.8 8.0	3.0 4.0	9.0 9.6	ns	Figures 3 & 6	
t_{set}	E_n to CP	2.5		2.0		2.5		ns	Figures 3 & 4	4
t_{hold}	E_n to CP	3.0		2.5		3.0		ns	Figures 3 & 4	
$t_{pw(H)}$	Pulse Width CP	2.5		2.5		5.0		ns	Figures 3 & 4	

Military Verison-Preliminary (Continued)

Cerpak TTL-to-ECL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$

Symbol	Parameter	$T_C = -55^\circ C$		$T_C = 25^\circ C$		$T_C = +125^\circ C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
f_{max}	Max Toggle Frequency	250		250		250		MHz		4
t_{PLH} t_{PHL}	CP to E_n	1.3	3.8	1.6	3.7	1.9	4.3	ns	Figures 1 & 2	1, 2, 3
t_{PZH}	OE to E_n (Cutoff to HIGH)	1.0	4.3	1.5	4.4	1.7	5.1	ns	Figures 1 & 2	
t_{PHZ}	OE to E_n (HIGH to Cutoff)	1.5	5.0	1.6	4.5	1.6	5.0	ns	Figures 1 & 2	
t_{PHZ}	DIR to E_n (HIGH to Cutoff)	1.6	4.7	1.6	4.3	1.7	4.7	ns	Figures 1 & 2	
t_{set}	T_n to CP	2.5		2.0		2.5		ns	Figures 1 & 2	4
t_{hold}	T_n to CP	2.5		2.0		2.5		ns	Figures 1 & 2	
$t_{pw(H)}$	Pulse Width CP	2.5		2.0		2.5		ns	Figures 1 & 2	
t_{TLH} t_{THL}	Transition Time 20% to 80%, 80% to 20%	0.4	2.3	0.5	2.1	0.4	2.4	ns	Figures 1 & 2	

Cerpak ECL-to-TTL AC Electrical Characteristics

$V_{EE} = -4.2V$ to $-5.7V$, $V_{TTL} = +4.5V$ to $+5.5V$, $C_L = 50$ pF

Symbol	Parameter	$T_C = -55^\circ C$		$T_C = 25^\circ C$		$T_C = +125^\circ C$		Units	Conditions	Notes
		Min	Max	Min	Max	Min	Max			
f_{max}	Max Toggle Frequency	200		200		100		MHz		4
t_{PLH} t_{PHL}	CP to T_n	3.1	8.0	3.1	7.3	3.3	8.0	ns	Figures 3 & 4	1, 2, 3
t_{PZH} t_{PZL}	OE to T_n (Enable Time)	3.4 3.7	9.1 9.5	3.7 4.0	9.0 9.3	4.0 4.3	10.1 10.4	ns	Figures 3 & 5	
t_{PHZ} t_{PLZ}	OE to T_n (Disable Time)	3.2 3.0	10.0 9.8	3.3 3.4	9.0 8.8	3.5 4.1	9.3 10.4	ns	Figures 3 & 5	
t_{PHZ} t_{PLZ}	DIR to T_n (Disable Time)	2.6 2.7	9.5 8.7	2.8 3.1	8.8 8.0	3.0 4.0	9.0 9.6	ns	Figures 3 & 6	
t_{set}	E_n to CP	2.5		2.0		2.5		ns	Figures 3 & 4	4
t_{hold}	E_n to CP	3.0		2.5		3.0		ns	Figures 3 & 4	
$t_{pw(H)}$	Pulse Width CP	2.5		2.5		5.0		ns	Figures 3 & 4	

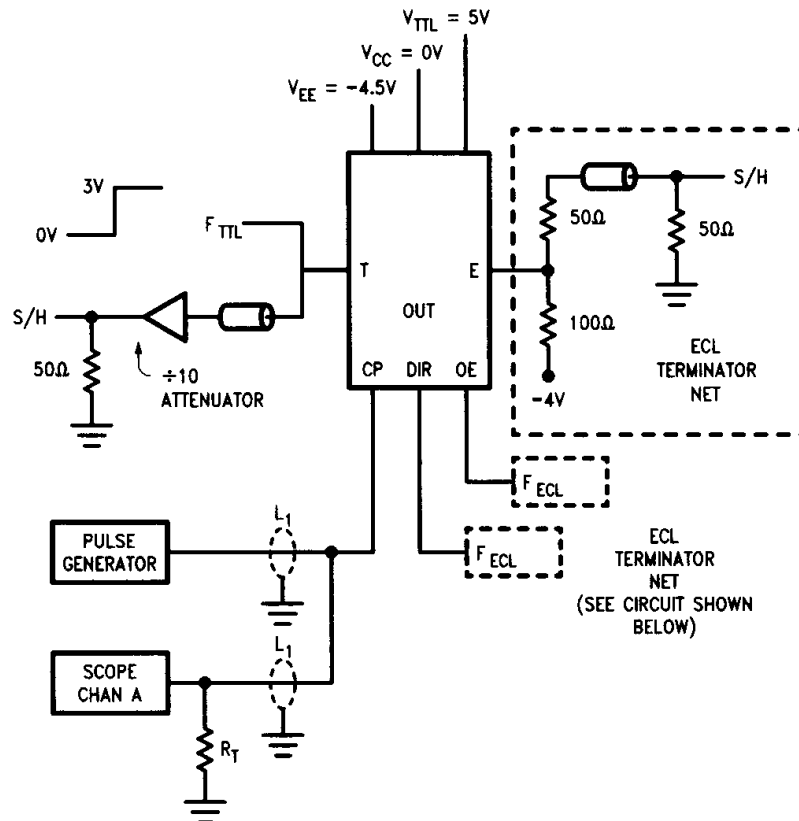
Note 1: F100K 300 Series cold temperature testing is performed by temperature soaking (to guarantee junction temperature equals $-55^\circ C$), then testing immediately after power-up. This provides "cold start" specs which can be considered a worst case condition at cold temperatures.

Note 2: Screen tested 100% on each device at $+25^\circ C$ temperature latched only, Subgroup A9.

Note 3: Sample tested (Method 5005, Table I) on each manufactured lot at $+25^\circ C$, Subgroup A9, and at $+125^\circ C$ and $-55^\circ C$ temperatures, Subgroups A10 and A11.

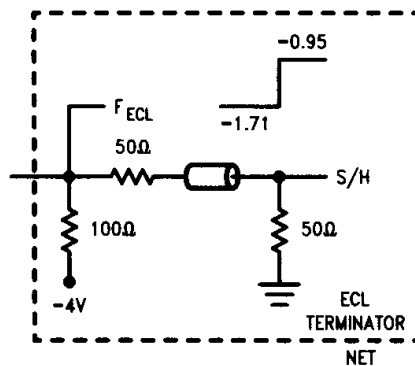
Note 4: Not tested at $+25^\circ C$, $+125^\circ C$, and $-55^\circ C$ temperature (design characterization data).

Test Circuitry



TL/F/10583-7

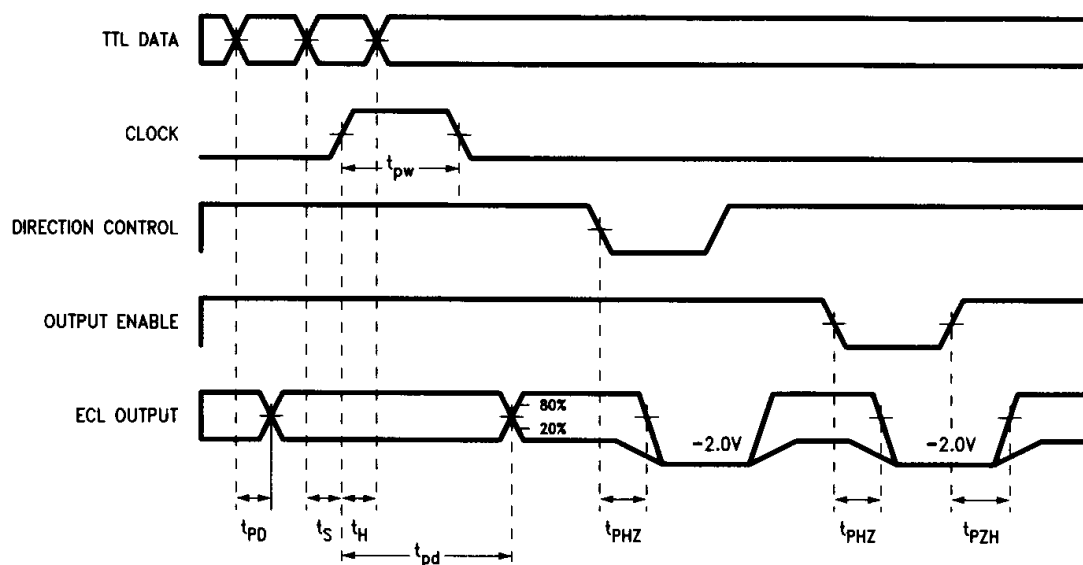
$R_T = 50\Omega$ termination of scope
 $L_1 = 50\Omega$ impedance lines



TL/F/10583-8

FIGURE 1. TTL to ECL AC Test Circuit

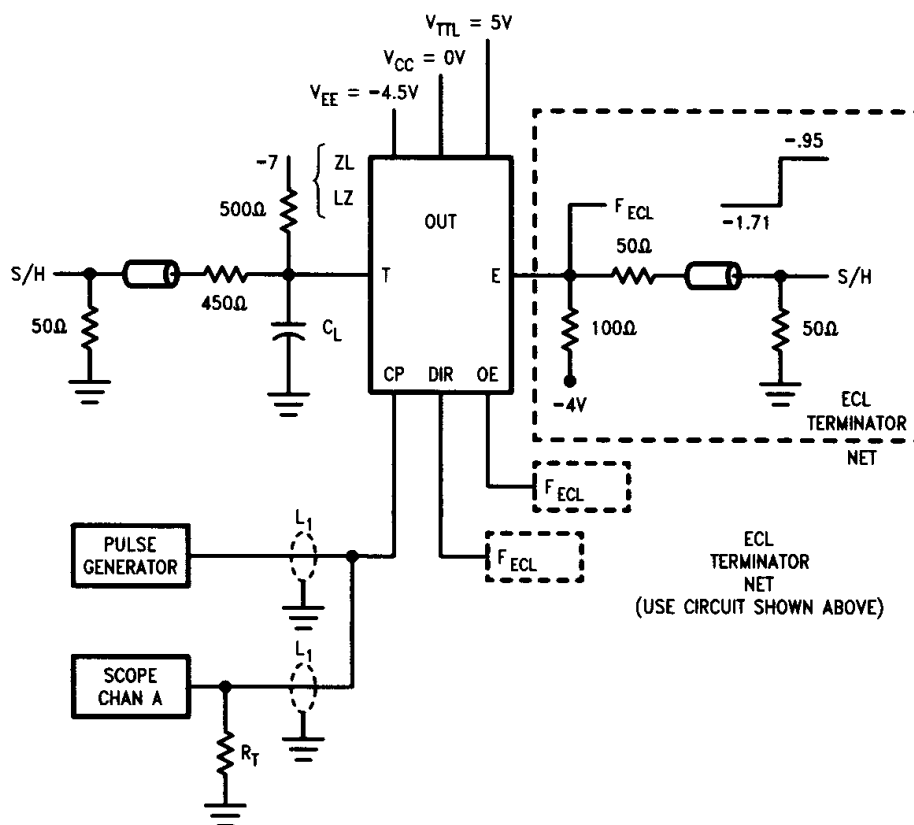
Switching Waveforms



TL/F/10583-9

FIGURE 2. TTL to ECL Transition—Propagation Delay and Transition Times

Test Circuit



$R_T = 50\Omega$ termination of scope

$L_1 = 50\Omega$ impedance lines

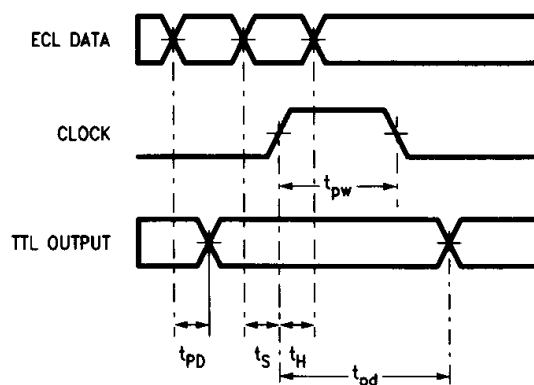
$C_L = 50$ pF including stray and jig capacitance.

Note: 50Ω to ground termination must be included on ECL I/O pins not monitored by a 50Ω scope to prevent oscillatory feedback.

TL/F/10583-10

FIGURE 3. ECL-to-TTL AC Test Circuit

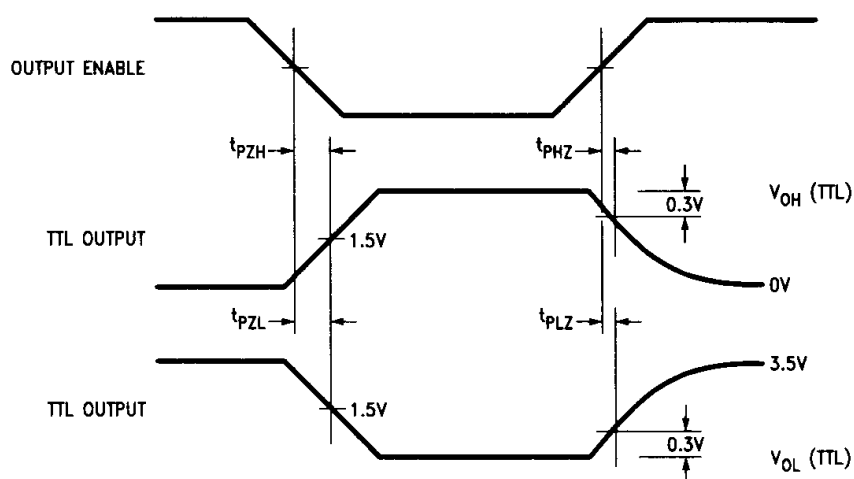
Switching Waveforms



Note: DIR is LOW, OE is HIGH

TL/F/10583-11

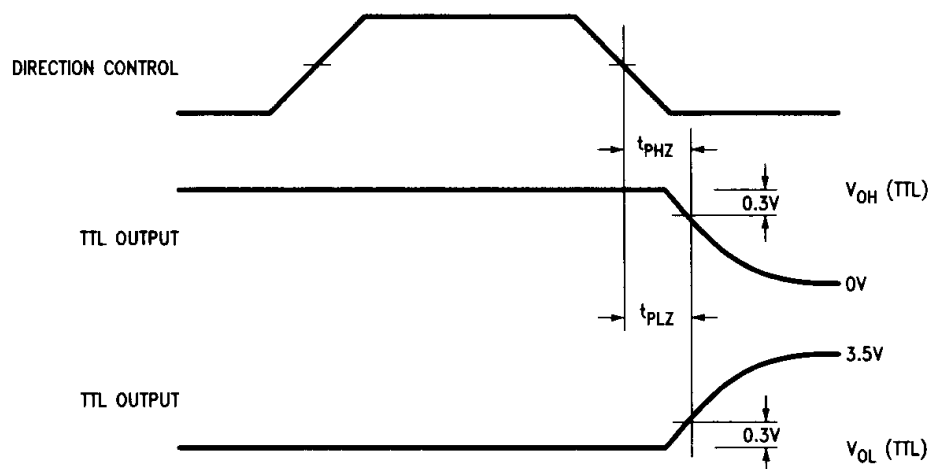
FIGURE 4. ECL-to-TTL Transition—Propagation Delay and Transition Times



Note: DIR is LOW

TL/F/10583-12

FIGURE 5. ECL-to-TTL Transition, OE to TTL Output, Enable and Disable Times



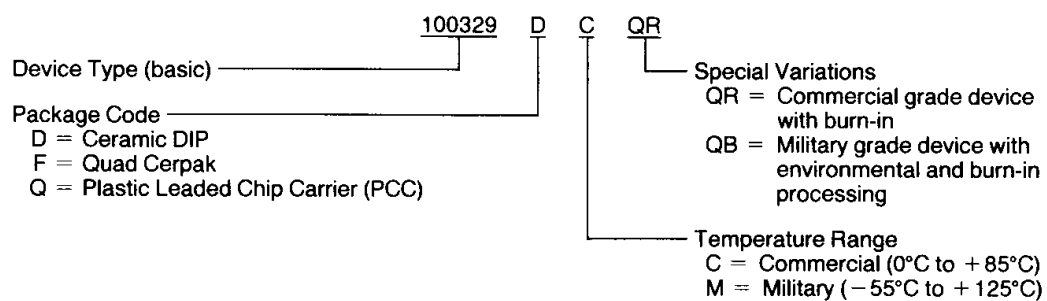
Note: OE is HIGH

TL/F/10583-13

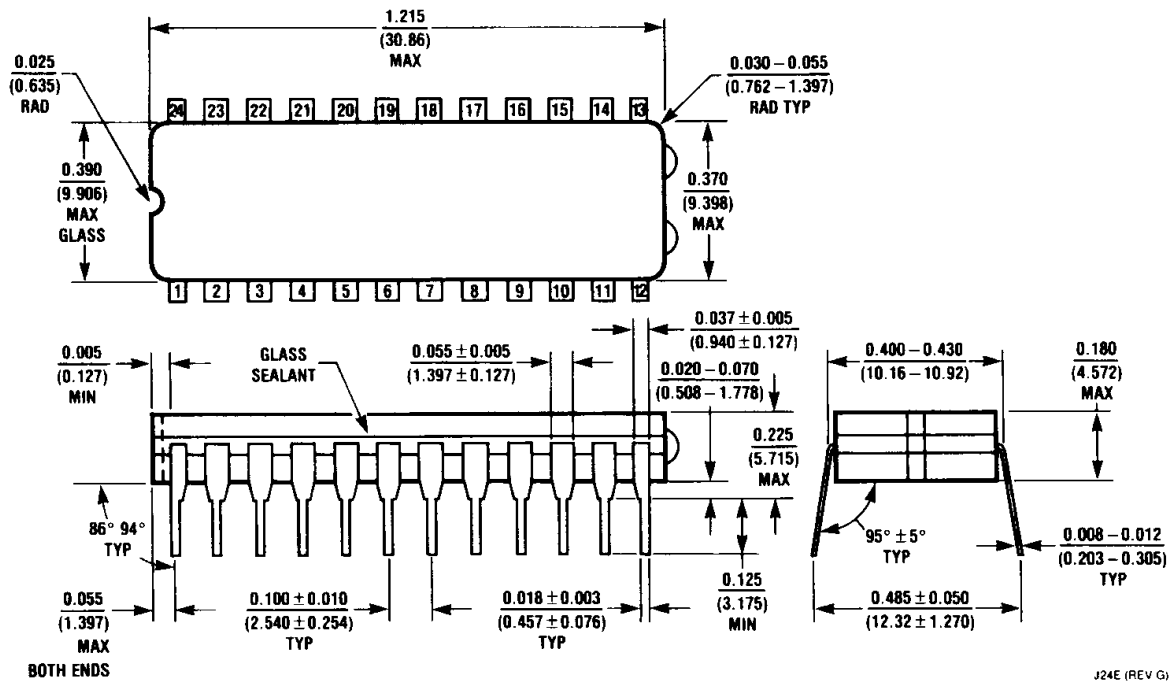
FIGURE 6. ECL-to-TTL Transition, DIR to TTL Output, Disable Time

Ordering Information

The device number is used to form part of a simplified purchasing code where a package type and temperature range are defined as follows:

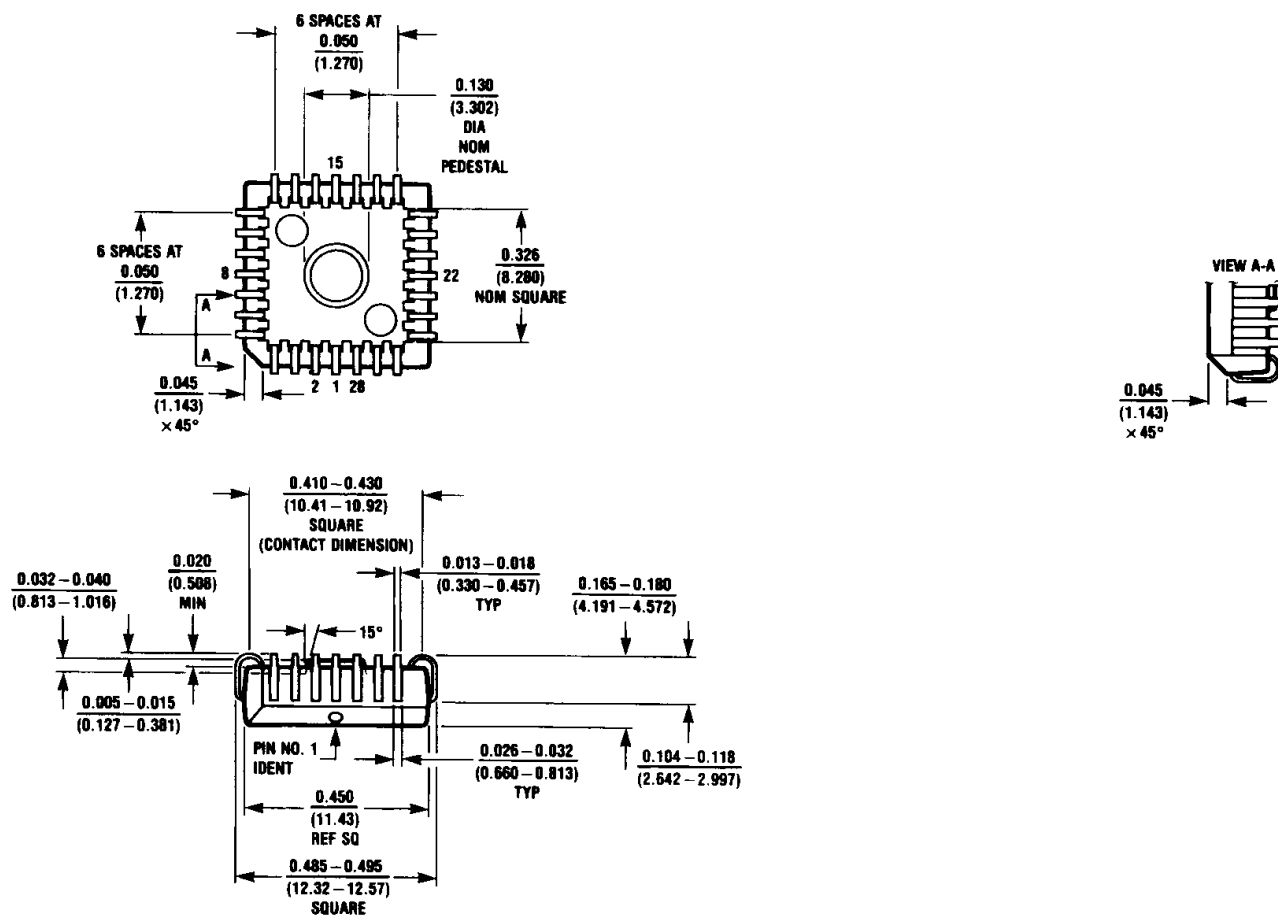


Physical Dimensions inches (millimeters)



**24-Lead Ceramic Dual-In-Line Package (0.400" Wide) (D)
NS Package Number J24E**

J24E (REV G)

Physical Dimensions inches (millimeters) (Continued)

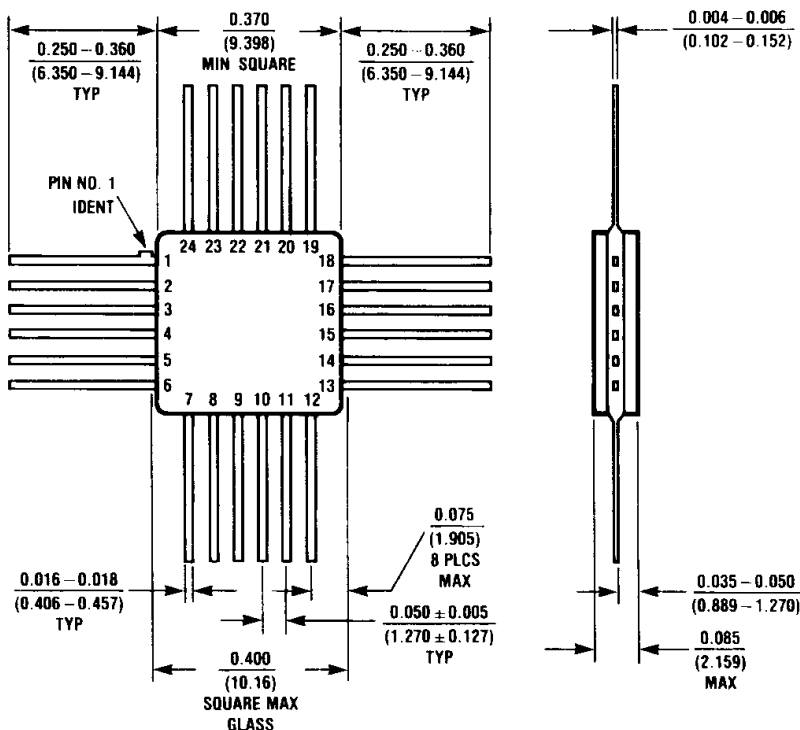
Note: Pedestal as shown on base is not available for F1000K ECL products

28-Lead Plastic Chip Carrier (Q)
NS Package Number V28A

V28A (REV G)

Physical Dimensions inches (millimeters) (Continued)

Lit. # 114910



W24B (REV C)

24-Lead Quad Cerpak (F)
NS Package Number W24B

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